

Title (en)  
Sheets of semiconductor material and methods for fabricating the same

Title (de)  
Folien aus Halbleitermaterial und Herstellungsverfahren dafür

Title (fr)  
Feuilles d'un matériau semi-conducteur et ses procédés de fabrication

Publication  
**EP 2091090 A2 20090819 (EN)**

Application  
**EP 08171563 A 20081212**

Priority  
US 3131808 A 20080214

Abstract (en)  
A sheet of semiconductor material (28) is provided, including a lower surface and an upper surface. The sheet of semiconductor material is fabricated by a process including forming a first layer (32) of silicon powder (34) that has a lower surface (36) and an opposite upper surface (38), depositing a second layer (40) across the upper surface of the first layer, wherein the second layer of silicon powder (42) has a lower surface (44) and an opposite upper surface (46) and has a substantially similar melting point to the first layer of silicon powder, and heating at least one of the first and second layers of silicon powder to initiate a controlled melt of one of the first and second layer of silicon powder and to initiate crystallization (43) of at least one of the first and second layers of silicon powder.

IPC 8 full level  
**H01L 31/18** (2006.01)

CPC (source: EP US)  
**H01L 31/1804** (2013.01 - EP US); **H01L 31/1872** (2013.01 - EP US); **Y02E 10/547** (2013.01 - EP US); **Y02P 70/50** (2015.11 - EP US); **Y10T 428/12028** (2015.01 - EP US)

Designated contracting state (EPC)  
AT BE BG CH CY CZ DE DK EE ES FI FR GB GR HR HU IE IS IT LI LT LU LV MC MT NL NO PL PT RO SE SI SK TR

Designated extension state (EPC)  
AL BA MK RS

DOCDB simple family (publication)  
**EP 2091090 A2 20090819**; AU 2008258140 A1 20090903; CN 101509143 A 20090819; US 2009208770 A1 20090820

DOCDB simple family (application)  
**EP 08171563 A 20081212**; AU 2008258140 A 20081215; CN 200810189563 A 20081212; US 3131808 A 20080214